

SMD Type 850nm Infrared Emitter

Features

- Small double-end package
- Viewing Angle at X axis (Note3) = ±55°
- High reliability
- Good spectral matching to Si photo detector
- RoHS compliance

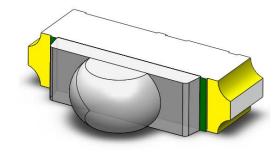
Applications

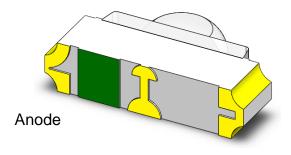
- Infrared sensor
- Infrared Touch Panel Solutions

Description

The HIRP2406W14-B10 is a GaAlAs infrared LED housed in a miniature SMD package. The device has a peak wavelength of 850nm LED spectrally matched with phototransistor or photodiode.

Package Outline





Cathode

Schematic



HIRP2406W14-B10 SMD Type 850nm Infrared Emitter

Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
lF	Continuous Forward Current	70	mA	
I _{FP}	Peak Forward Current	0.7	Α	1
V _R	Reverse Voltage	5	V	
T _{opr}	Operating Temperature	-40 ~ +85	°C	
T _{stg}	Storage Temperature	-40 ~ +100	°C	
T _{sol}	Soldering Temperature	260	°C	2
P _D	Power Dissipation at(or below) 25°C Free Air Temperature	140	mW	
R _{THJA}	Junction to Ambient Thermal Resistance	540	°C/W	

Electro-Optical Characteristics TA = 25°C (unless otherwise specified)

Optical Characteristics

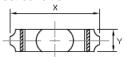
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
le	Radiant Intensity	I _F =20mA	2.50	4.0	-	\\\/o=	
		I _F =70mA	-	13.5	-	mW/sr	
λр	Peak Wavelength	I _F =20mA	-	850	-	nm	
Δλ	Spectral Bandwidth	I _F =20mA	-	30	-	nm	
θ1/2	Angle of Half Intensity (X)	IF=20mA	-	±55.0	-	dog	3
	Angle of Half Intensity (Y)	I⊦=∠UIIA	-	±25.0	-	- deg	

Electrical Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
V Forward Voltage		I _F =20mA	1.30	1.49	1.7	- v	
V _F Forward Voltage	I _F =70mA	1.40	1.67	2.0			
I _R	Reverse Current	V _R =5V	-	•	10	μA	

Notes:

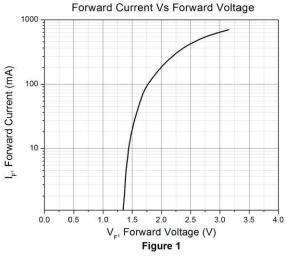
- 1 : I_{FP} Conditions--Pulse Width $\leq~100\mu s$ and Duty $\leq~1\%.$
- 2 : Soldering time $\leq\!\!5$ seconds.
- 3: Test condition:

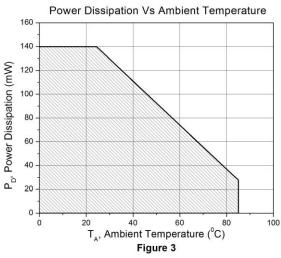


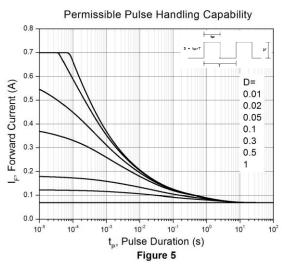


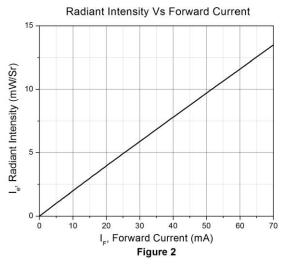
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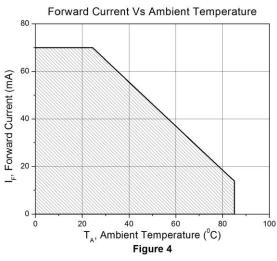
Typical Characteristic Curves

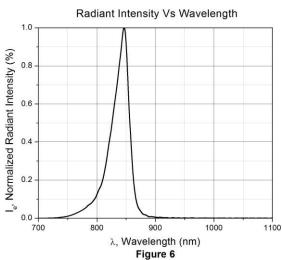










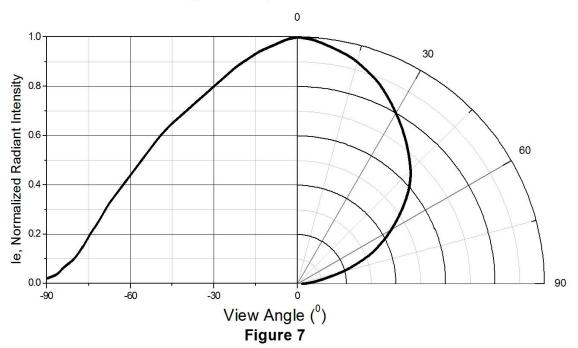




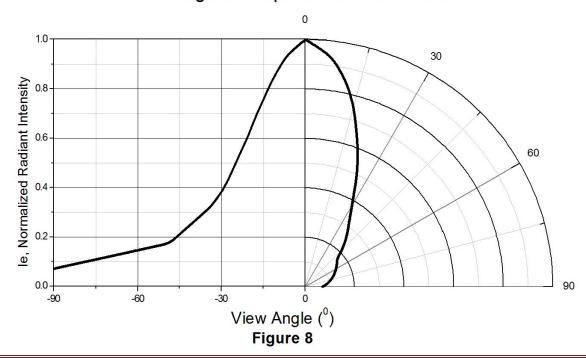
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Typical Characteristic Curves

Angular Displacement at X axis



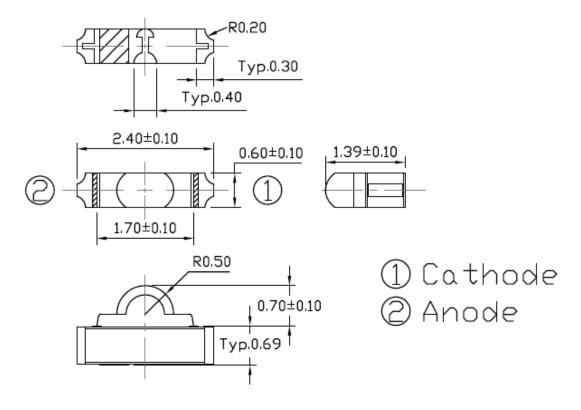
Angular Displacement at Y axis



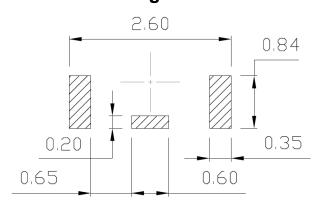


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Package Dimension All dimensions are in mm, unless otherwise stated



Recommended Soldering Mask All dimensions are in mm, unless otherwise stated



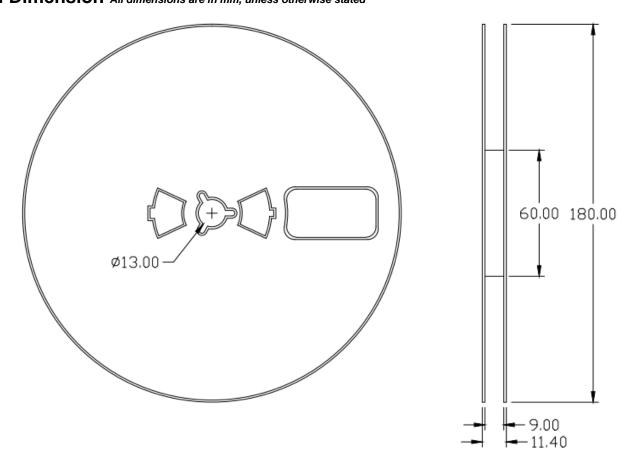
Ordering Information

Part Number	Description	Quantity
HIRP2406W14-B10	Tape & Reel	5000 pcs

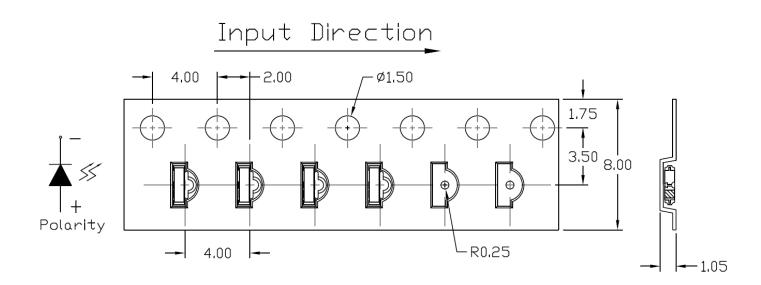


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Reel Dimension All dimensions are in mm, unless otherwise stated



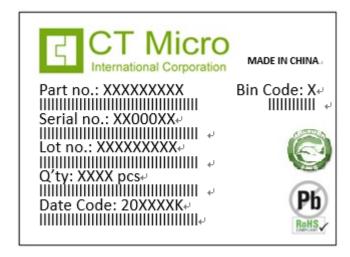
Tape Dimension All dimensions are in mm, unless otherwise stated





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Label Form Specification



Part no: CTM Production Number Serial no: Production Number

Lot no: Lot number

Q'ty: Packing Quantity

Date Code: Manufacture Date

Bin Code: le Ranks

MADE IN CHINA: Production Place

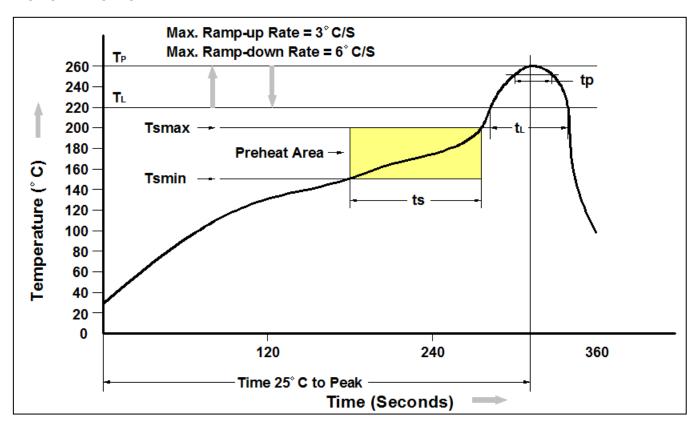
Storage Condition

- 1. Do not open moisture proof bag before the products are ready to use.
- 2. The moisture barrier bag should be stored at 30°C and 90%R.H. max. before opening. Shelf life of non-opened bag is 12 months after the bag sealing date.
- 3. After opening the moisture barrier bag floor life is 168h at 30°C/60%RH. max. Unused LEDs should be resealed into moisture barrier bag. (Refer to J-STD-020 Standard)
- 4. If the moisture absorbent material has faded away or the LEDs have exceeded the storage time, baking treatment should be performed using the J-STD-033 Standard conditions.



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Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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